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BUK9277-55A

N-channel TrenchMOS logic level FET

12 June 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	55	V
I_D	drain current	$V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 2 ; Fig. 3	-	-	18	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ Fig. 1	-	-	51	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C}$	-	59	69	mΩ
		$V_{GS} = 4.5\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C}$	-	-	86	mΩ
		$V_{GS} = 5\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C};$ Fig. 13	-	65	77	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 18\text{ A}; V_{sup} \leq 55\text{ V}; R_{GS} = 50\text{ Ω};$ $V_{GS} = 5\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped	-	-	33	mJ



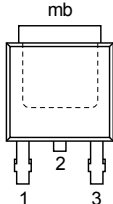
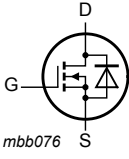
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BUK9277-55A

N-channel TrenchMOS logic level FET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p style="text-align: center;">DPAK (SOT428)</p>	 <p style="text-align: center;">mbb076</p>
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9277-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428
BUK9277-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9277-55A	BUK9277-55A
BUK9277-55A/CD	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-15	15	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	51	W
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 2 ; Fig. 3	-	18	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 2	-	13	A

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BUK9277-55A

N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3	-	73	A
T_{stg}	storage temperature		-55	175	$^{\circ}\text{C}$
T_j	junction temperature		-55	175	$^{\circ}\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	18	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$	-	73	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 18\text{ A}$; $V_{sup} \leq 55\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; unclamped	-	33	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	Fig. 4	[1][2][3][4]	-	J

- [1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}$.
- [3] Repetitive avalanche rating limited by an average junction temperature of 170 $^{\circ}\text{C}$.
- [4] Refer to application note AN10273 for further information.

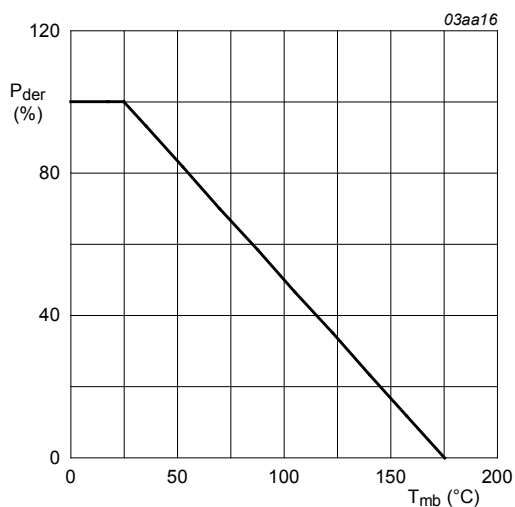


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

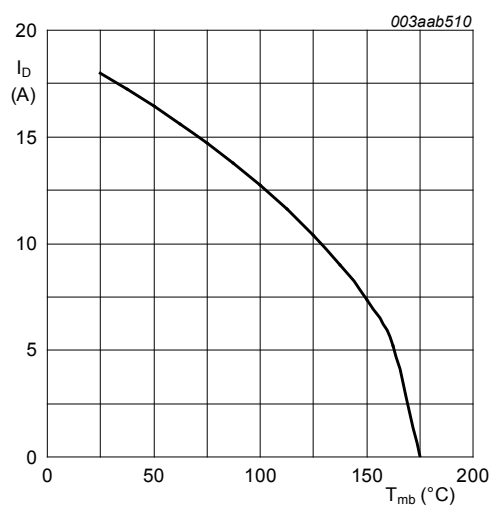


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5\text{ V}$$

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N-channel TrenchMOS logic level FET

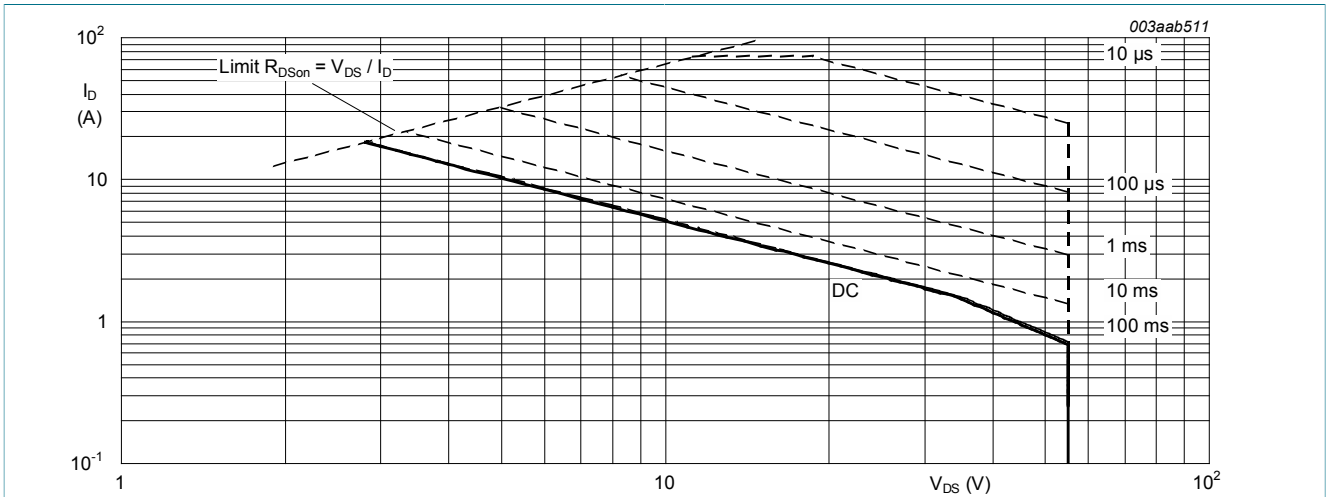


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}; I_{DM}$ is single pulse

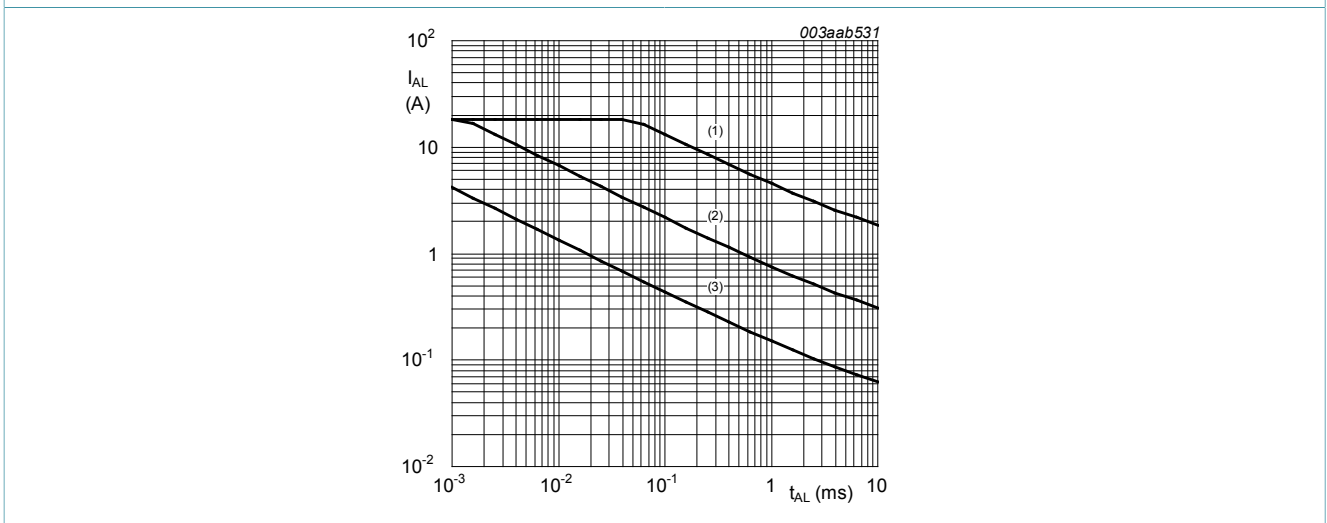


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

- (1) Single-pulse; $T_j = 25\text{ }^{\circ}\text{C}$.
- (2) Single-pulse; $T_j = 150\text{ }^{\circ}\text{C}$.
- (3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	2.93	K/W

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BUK9277-55A

N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	71.4	-	K/W

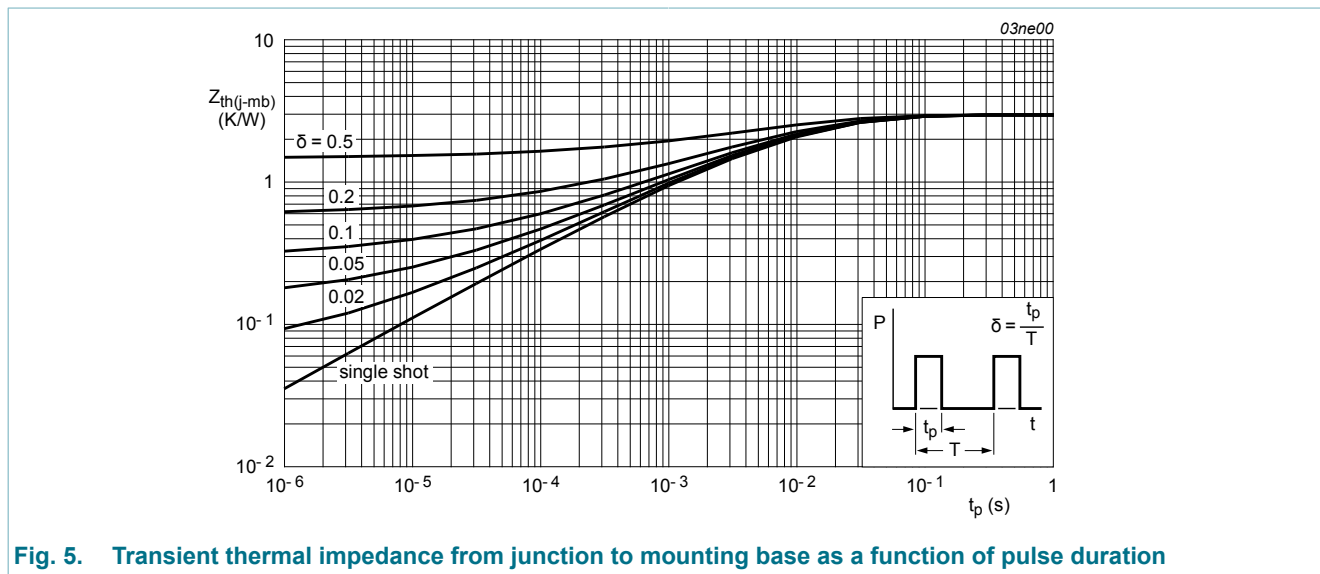


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	55	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ Fig. 12	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 12	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ Fig. 12	0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	59	69	m Ω
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	86	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ Fig. 13	-	-	154	m Ω

NXP Semiconductors

BUK9277-55A

N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = 5\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 13	-	65	77	mΩ
Dynamic characteristics						
$Q_{G(\text{tot})}$	total gate charge	$I_D = 10\text{ A}; V_{DS} = 44\text{ V}; V_{GS} = 5\text{ V};$ Fig. 14	-	11	-	nC
Q_{GS}	gate-source charge		-	1.6	-	nC
Q_{GD}	gate-drain charge		-	5	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 15	-	440	643	pF
C_{oss}	output capacitance		-	90	110	pF
C_{rss}	reverse transfer capacitance		-	60	93	pF
$t_{d(\text{on})}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.2\text{ }^\Omega; V_{GS} = 5\text{ V};$ $R_{G(\text{ext})} = 10\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	10	-	ns
t_r	rise time		-	47	-	ns
$t_{d(\text{off})}$	turn-off delay time		-	28	-	ns
t_f	fall time		-	33	-	ns
L_D	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25\text{ }^\circ\text{C}$	-	2.5	-	nH
L_S	internal source inductance	measured from source lead from package to source bond pad; $T_j = 25\text{ }^\circ\text{C}$	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s};$ $V_{GS} = -10\text{ V}; V_{DS} = 30\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	33	-	ns
Q_r	recovered charge		-	60	-	nC

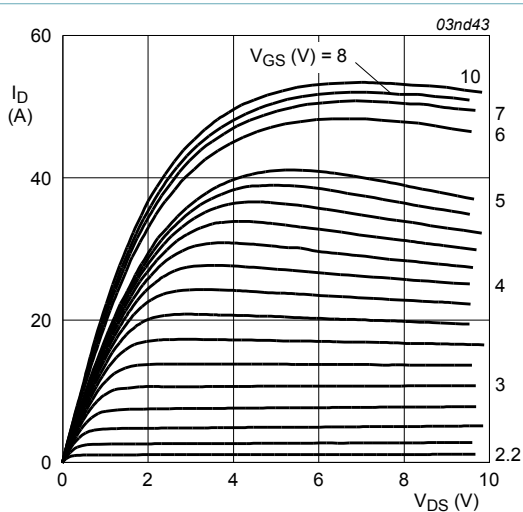


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}; t_p = 300\mu\text{s}$

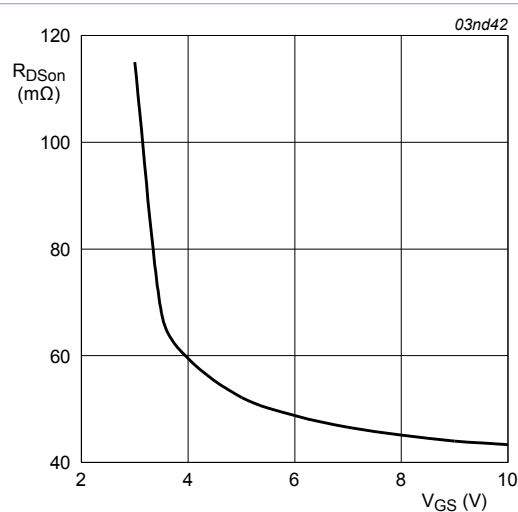


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$

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N-channel TrenchMOS logic level FET

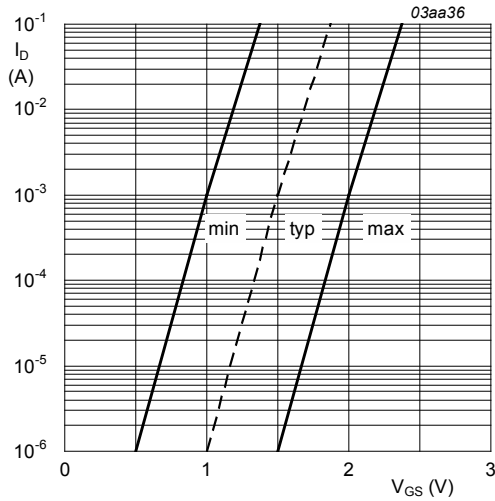


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = V_{GS}$

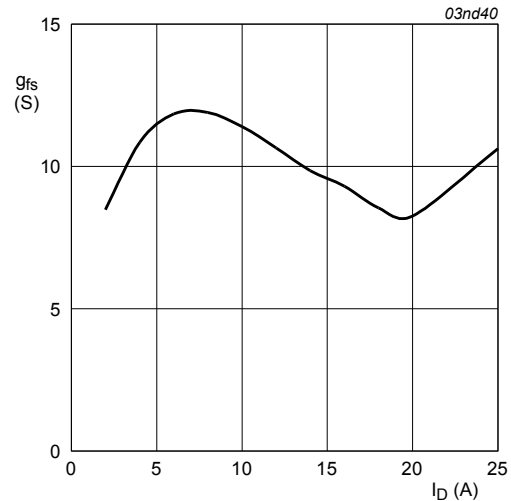


Fig. 9. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

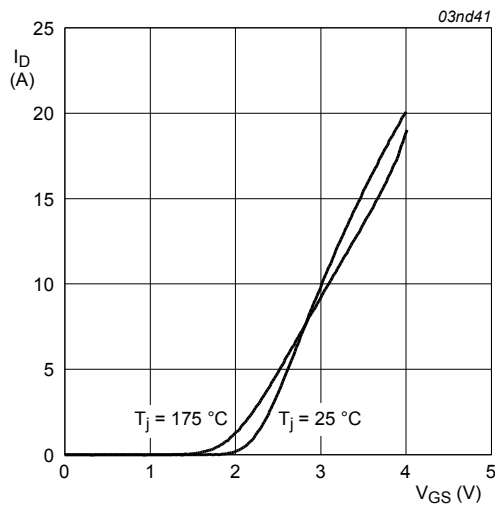


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25\text{V}$

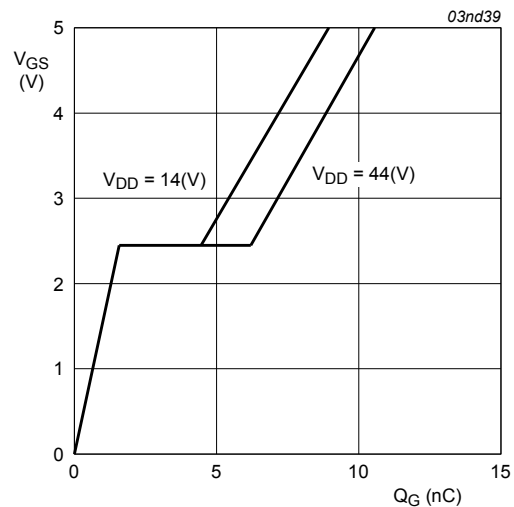


Fig. 11. Gate-source voltage as a function of turn-on gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 10\text{A}$

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N-channel TrenchMOS logic level FET

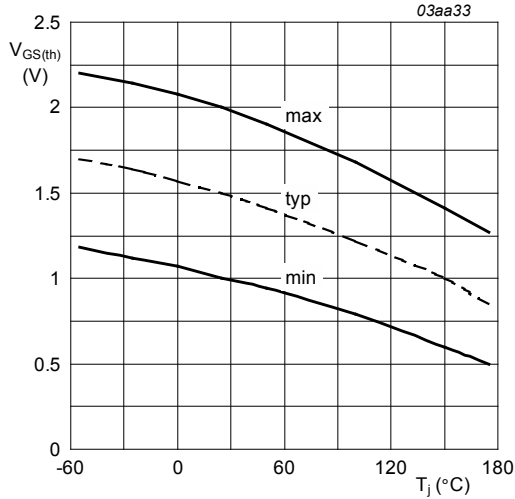


Fig. 12. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

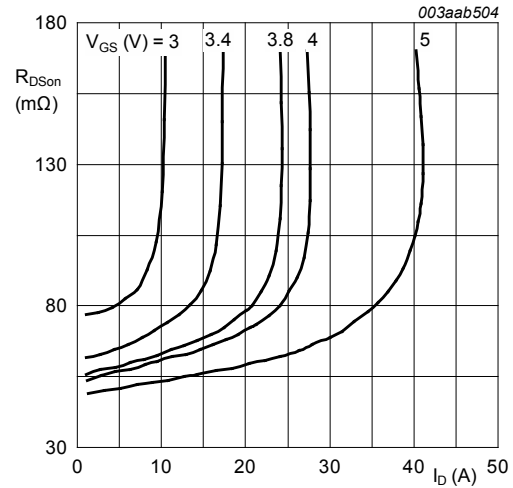


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

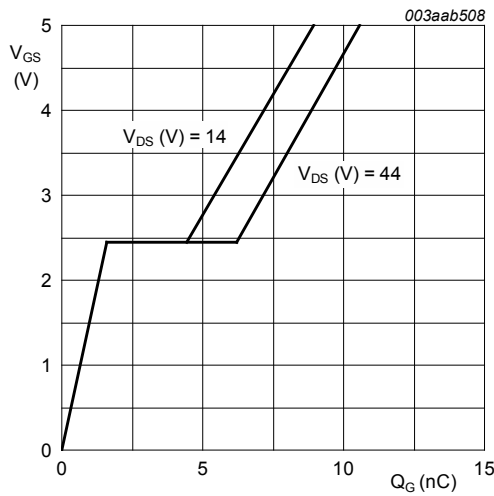


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ\text{C}; I_D = 10\text{A}$$

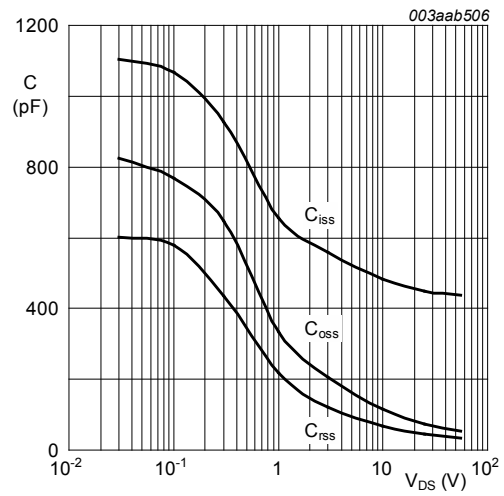


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

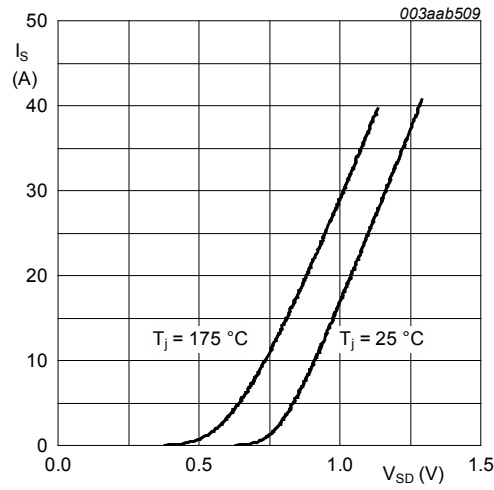


Fig. 16. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

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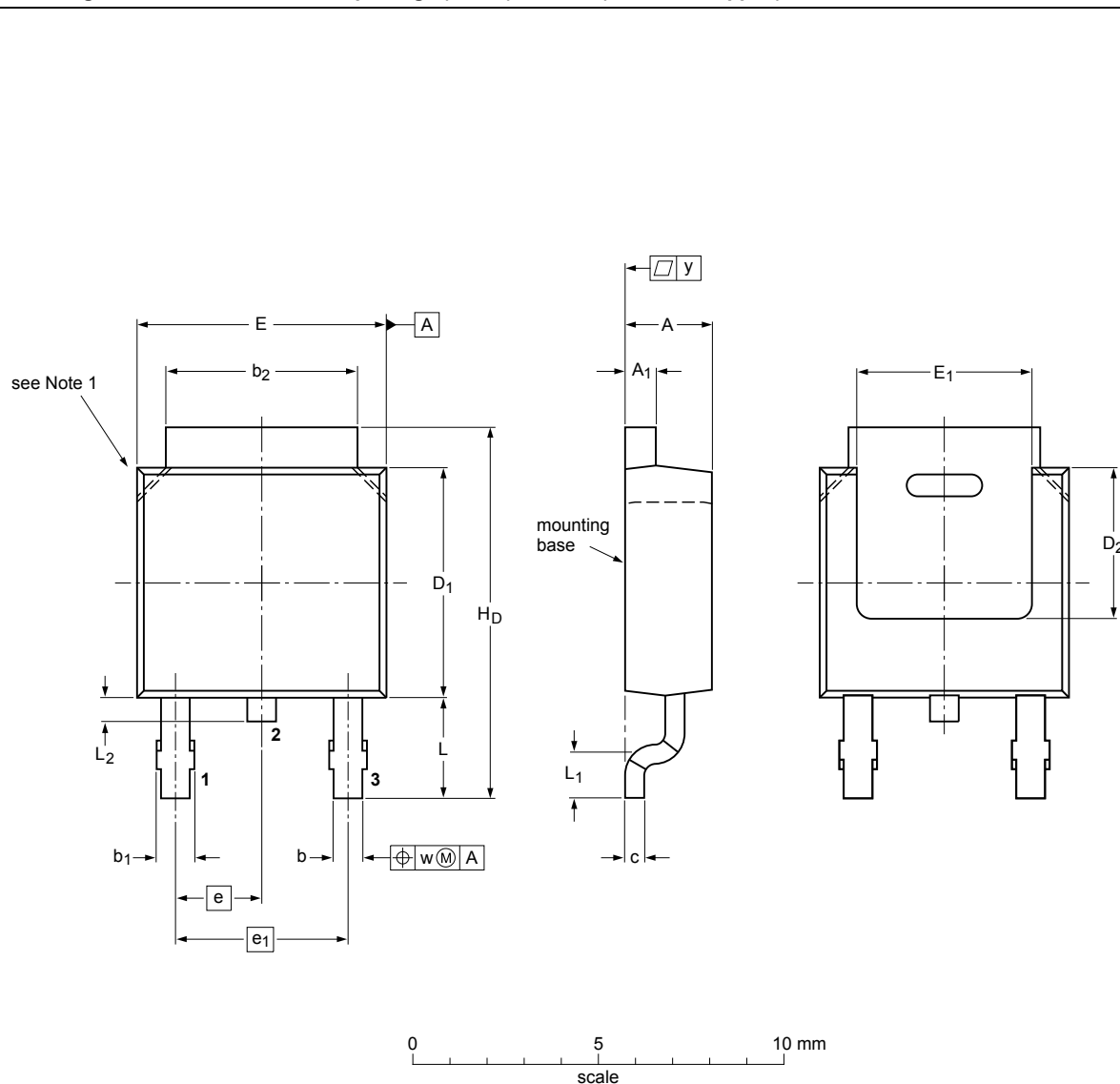
BUK9277-55A

N-channel TrenchMOS logic level FET

11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₁	b ₂	c	D ₁	D ₂	E	E ₁	e	e ₁	H _D	L	L ₁	L ₂	w	y
max	2.38	0.93	0.89	1.1	5.46	0.56	6.22		6.73				10.4	2.95		0.9		0.2
nom											2.285	4.57					0.2	
min	2.22	0.46	0.71	0.9	5.00	0.20	5.98	4.0	6.47	4.45			9.6	2.55	0.5	0.5		

Note
 1. Plastic body may have 45° chamfer.

sot428_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT428		TO-252	SC-63			-06-03-16- 14-06-10

Fig. 17. Package outline DPAK (SOT428)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
 [2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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